

Ngoc Thanh Duong

List of Publications by Year in descending order

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Version: 2024-02-01

16
papers

530
citations

840776

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940533

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docs citations

16
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903
citing authors

#	ARTICLE	IF	CITATIONS
1	Achieving direct electrophoretically deposited highly stable polymer induced CsPbBr ₃ colloidal nanocrystal films for high-performance optoelectronics. <i>Chemical Engineering Journal</i> , 2022, 433, 133809.	12.7	14
2	Gate tunable photoresponse of a two-dimensional p-n junction for high performance broadband photodetector. <i>Applied Materials Today</i> , 2022, 26, 101285.	4.3	7
3	Carrier transport through near-ideal interface for WSe ₂ van der Waals homojunction diode. <i>Applied Surface Science</i> , 2021, 542, 148499.	6.1	3
4	Patterning of type-II Dirac semimetal PtTe ₂ for optimized interface of tellurene optoelectronic device. <i>Nano Energy</i> , 2021, 86, 106049.	16.0	22
5	Large Area MoS ₂ via Colloidal Nanosheet Ink for Integrated Memtransistor. <i>Small Methods</i> , 2021, 5, 2100558.	8.6	8
6	Gate-controlled MoTe ₂ homojunction for sub-thermionic subthreshold swing tunnel field-effect transistor. <i>Nano Today</i> , 2021, 40, 101263.	11.9	19
7	Interface Trap Suppression and Electron Doping in Van der Waals Materials Using Cross-Linked Poly(vinylpyrrolidone). <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 55489-55497.	8.0	1
8	Modulation of Junction Modes in SnSe ₂ /MoTe ₂ Broken-Gap van der Waals Heterostructure for Multifunctional Devices. <i>Nano Letters</i> , 2020, 20, 2370-2377.	9.1	75
9	Contact Engineering of Layered MoS ₂ via Chemically Dipping Treatments. <i>Advanced Functional Materials</i> , 2020, 30, 2000250.	14.9	14
10	Encapsulation of a Monolayer WSe ₂ Phototransistor with Hydrothermally Grown ZnO Nanorods. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 20257-20264.	8.0	15
11	Modulating the Functions of MoS ₂ /MoTe ₂ van der Waals Heterostructure via Thickness Variation. <i>ACS Nano</i> , 2019, 13, 4478-4485.	14.6	85
12	Suppressing Ambipolar Characteristics of WSe ₂ Field Effect Transistors Using Graphene Oxide. <i>Advanced Electronic Materials</i> , 2019, 5, 1800608.	5.1	8
13	Highly Enhanced Photoresponsivity of a Monolayer WSe ₂ Photodetector with Nitrogen-Doped Graphene Quantum Dots. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 10322-10329.	8.0	114
14	Augmented Quantum Yield of a 2D Monolayer Photodetector by Surface Plasmon Coupling. <i>Nano Letters</i> , 2018, 18, 2316-2323.	9.1	82
15	Photovoltaic effect in a few-layer ReS ₂ /WSe ₂ heterostructure. <i>Nanoscale</i> , 2018, 10, 20306-20312.	5.6	38
16	Parameter control for enhanced peak-to-valley current ratio in a MoS ₂ /MoTe ₂ van der Waals heterostructure. <i>Nanoscale</i> , 2018, 10, 12322-12329.	5.6	25